

1214-300M

300 Watts - 40 Volts, 150µs, 10% Radar 1200 - 1400 MHz

GENERAL DESCRIPTION

The 1214-300M is an internally matched, COMMON BASE transistor capable of providing 300 Watts of pulsed RF output power at one hundred fifty microseconds pulse width, ten percent duty factor across the band 1200 to 1400 MHz. This hermetically solder-sealed transistor is specifically designed for L-Band radar applications. It utilizes gold metalization and NiCr emitter ballasting to provide high reliability and supreme ruggedness.

ABSOLUTE MAXIMUM RATINGS

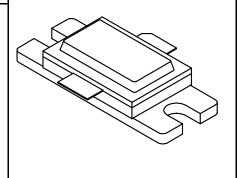
Maximum Power Dissipation @ 25°C 600 Watts

Maximum Voltage and Current

BVces Collector to Emitter Voltage 70 Volts
BVebo Emitter to Base Voltage 3.5 Volts
Ic Collector Current 20 Amps

Maximum Temperatures

Storage Temperature $-65 \text{ to} + 200^{\circ}\text{C}$ Operating Junction Temperature $+200^{\circ}\text{C}$ CASE OUTLINE 55ST, STYLE 1



ELECTRICAL CHARACTERISTICS @ 25 °C

SYMBOL	CHARACTERISTICS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Pout Pg ηc Rl VSWR ¹ VSWRs	Power Out Power Gain Collector Efficiency Input Return loss Load Mismatch Tolerance Load Mismatch - Stability	Freq = 1200 – 1400 MHz Vcc = 40 Volts Pin = 40 Watts Pulse Width = 150µs Duty Factor = 10%	300 8.75 50 10.0	55	2:1 1.5:1	Watts dB % dB

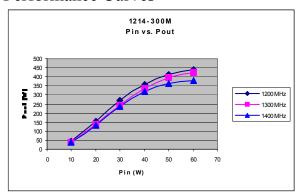
Note 1: Pulse condition of 150µsec, 10%.

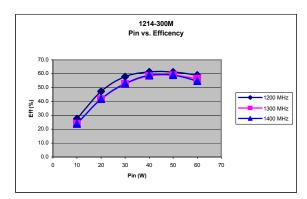
Bvces Ices	Collector to Emitter Breakdown Collector to Emitter Leakage	Ic = 80 mA Vce = 40 Volts	70	10	Volts mA
θjc ¹	Thermal Resistance	Rated Pulse Condition		0.29	°C/W

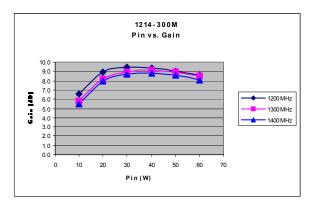


1214-300M

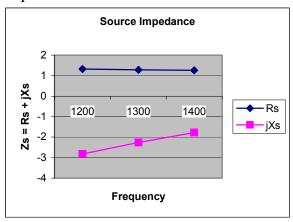
Performance Curves

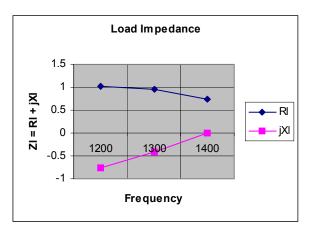




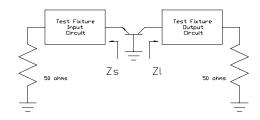


Impedance Information





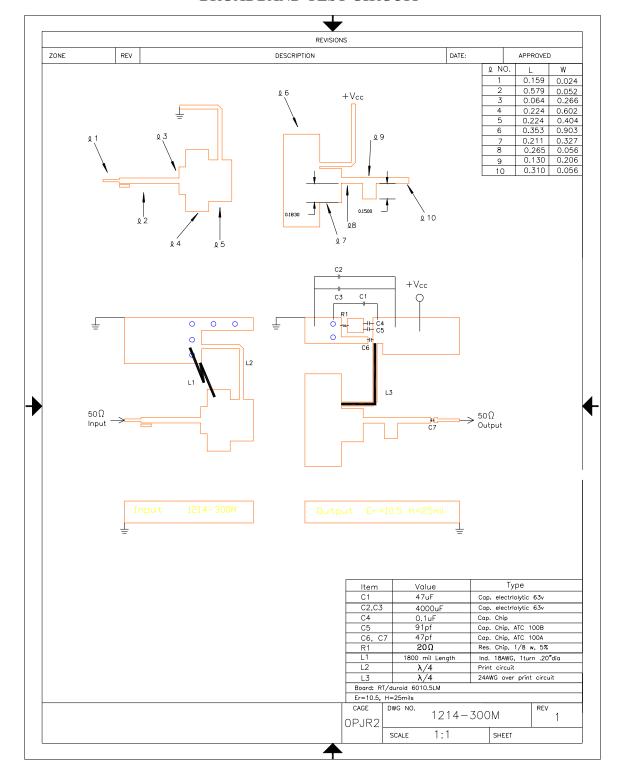
Impedance						
Freq	Zs	ZI				
1200	1.32-j2.82	1.03-j0.75				
1300	1.28-j2.26	0.95-j0.41				
1400	1.26-j1.78	0.75-j0.00				





1214-300M

BROADBAND TEST CIRCUIT





1214–300M

